

# 5<sup>th</sup> Generation CoolSiC™ 1200V Schottky Diode

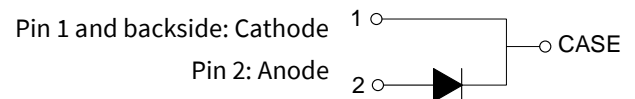
## SiC Diode

### Features

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery current / no forward recovery
- Temperature independent switching behaviour
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Excellent thermal performance
- Extended surge current capability
- Specified dv/dt ruggedness
- Pb-free lead plating; RoHS compliant



### Pin definition



### Potential applications

- Drives
- Industrial power supplies: Industrial UPS
- Solar central inverters and Solar string inverter

### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

### Description

- System efficiency improvement over Si diodes
- Enabling higher frequency / increased power density solutions
- System size/cost savings due to reduced heatsink requirements and smaller magnetics
- Reduced EMI
- Highest efficiency across the entire load range
- Robust diode operation during surge events
- High reliability
- Related Links: [www.infineon.com/SiC](http://www.infineon.com/SiC)



### Key performance parameters

Type	V <sub>DC</sub>	I <sub>F</sub>	Q <sub>C</sub>	T <sub>vj,max</sub>	Marking	Package
IDK16G120C5	1200 V	16 A	57nC	175°C	D1612C5	PG-TO263-2



## Table of contents

Features .....	1
Potential applications .....	1
Product validation .....	1
Description .....	1
Key performance parameters.....	1
Table of contents.....	2
1 Maximum ratings .....	3
2 Thermal resistances .....	5
3 Electrical Characteristics .....	6
4 Electrical Characteristics Diagrams .....	7
5 Package Drawing .....	10
Revision history.....	11

Maximum ratings

## 1 Maximum ratings

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage $T_C \geq 25^\circ\text{C}$	$V_{RRM}$	1200	V
Continuous forward current for $R_{th(j-c,max)}$ $T_C = 145^\circ\text{C}, D=1$ $T_C = 135^\circ\text{C}, D=1$ $T_C = 25^\circ\text{C}, D=1$	$I_F$	16 19 40	A
Surge repetitive forward current, sine halfwave <sup>1</sup> $T_C=25^\circ\text{C}, t_p=10\text{ms}$ $T_C=100^\circ\text{C}, t_p=10\text{ms}$	$I_{F,RM}$	64 48	A
Surge non-repetitive forward current, sine halfwave $T_C=25^\circ\text{C}, t_p=10\text{ms}$ $T_C=150^\circ\text{C}, t_p=10\text{ms}$	$I_{F,SM}$	140 120	A
Non-repetitive peak forward current $T_C = 25^\circ\text{C}, t_p=10 \mu\text{s}$	$I_{F,max}$	850	A
$i^2t$ value $T_C = 25^\circ\text{C}, t_p=10 \text{ms}$ $T_C = 150^\circ\text{C}, t_p=10 \text{ms}$	$\int i^2 dt$	99 71	$\text{A}^2\text{s}$
Diode $dv/dt$ ruggedness $V_R=0\dots960 \text{V}$	$dv/dt$	80	V/ns
Power dissipation for $R_{th(j-c,max)}$ $T_C = 25^\circ\text{C}$	$P_{tot}$	250	W

<sup>1</sup> Not subject to production test. The test was performed with 20000 pulses (two consecutive half-wave rectified sines with 10 ms period).

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### Maximum ratings

Operating temperature	$T_{vj}$	-55...175	°C
Storage temperature	$T_{stg}$	-55...150	°C
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STD-020)	$T_{sold}$	260	°C

## 2 Thermal resistances

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Characteristic</b>						
Diode thermal resistance, junction – case	$R_{th(j-c)}$		-	0.46	0.60	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	Leaded	-	-	62	K/W

### 3 Electrical Characteristics

#### Static Characteristics, at $T_{vj}=25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
DC blocking voltage	$V_{DC}$	$T_{vj} = 25^{\circ}\text{C}, I_R=50\mu\text{A}$	1200	-	-	V
Diode forward voltage	$V_F$	$I_F=16\text{A}, T_{vj}=25^{\circ}\text{C}$	-	1.65	1.95	V
		$I_F=16\text{A}, T_{vj}=150^{\circ}\text{C}$	-	2.25	-	
Reverse current	$I_R$	$V_R=1200\text{V}, T_{vj}=25^{\circ}\text{C}$	-	5.5	80	$\mu\text{A}$
		$V_R=1200\text{V}, T_{vj}=150^{\circ}\text{C}$	-	28	-	

#### Dynamic Characteristics, at $T_{vj}=25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Total capacitive charge	$Q_C$	$V_R = 800\text{V}, T_{vj}=150^{\circ}\text{C}$ $Q_C = \int_0^{V_R} C(V)dV$	-	57	-	nC
Total Capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$	-	730	-	pF
		$V_R=400\text{V}, f=1\text{MHz}$	-	52	-	
		$V_R=800\text{V}, f=1\text{MHz}$	-	40	-	

## 4 Electrical Characteristics Diagrams

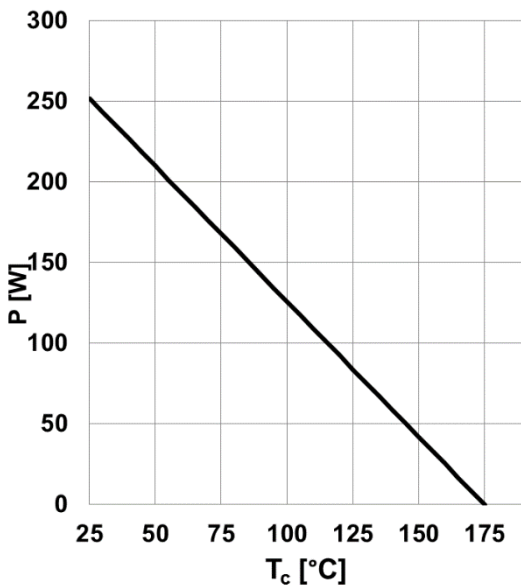


Figure 1. Power dissipation as function of case temperature,  $P_{tot}=f(T_c)$ ,  $R_{th(j-c),max}$

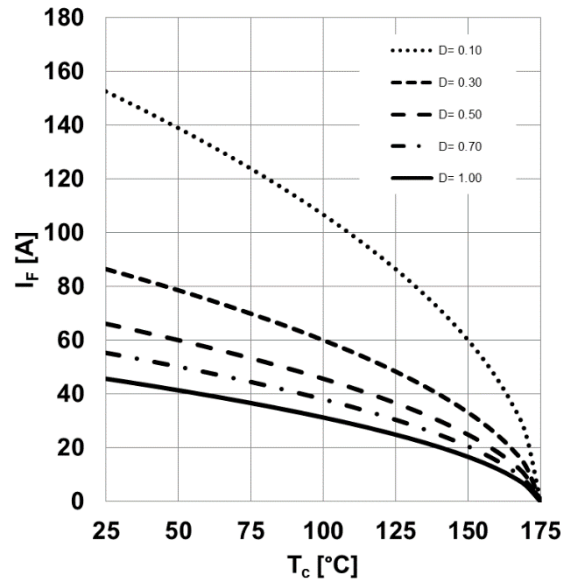


Figure 2. Diode forward current as function of temperature, parameter:  $T_{vj} \leq 175^\circ\text{C}$ ,  $R_{th(j-c),max}$ ,  $D$ =duty cycle,  $V_{th}$ ,  $R_{diff}$  @  $T_{vj}=175^\circ\text{C}$

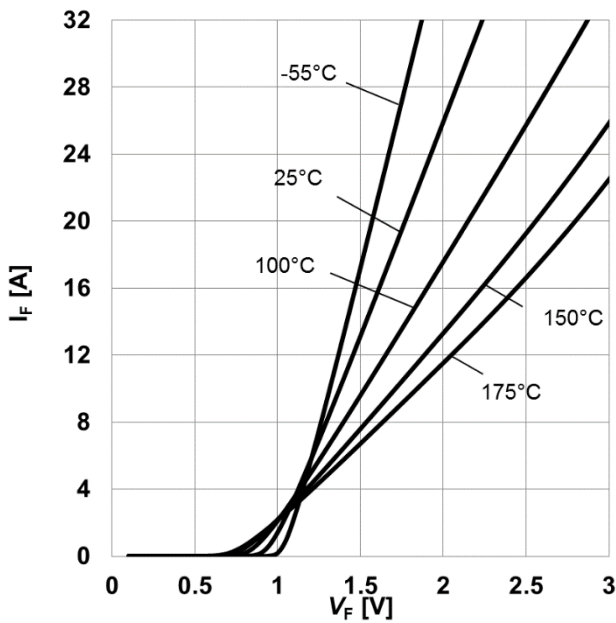


Figure 3. Typical forward characteristics,  $I_F=f(V_F)$ ,  $t_p=10 \mu\text{s}$ , parameter:  $T_{vj}$

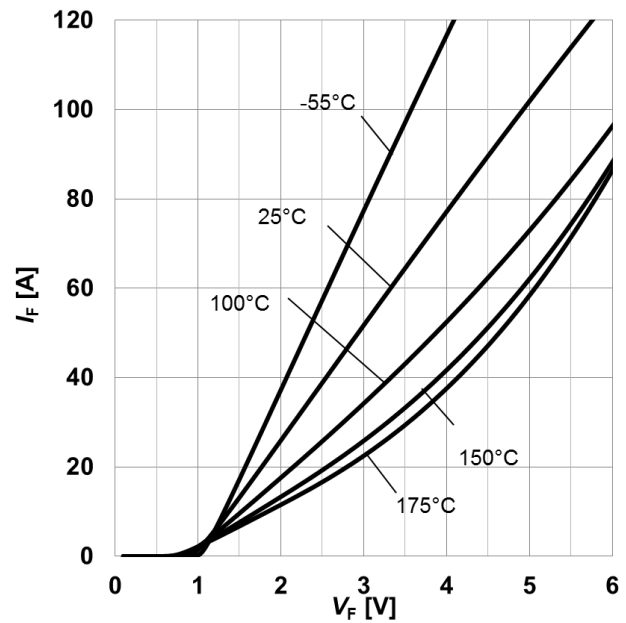


Figure 4. Typical forward characteristics in surge current,  $I_F=f(V_F)$ ,  $t_p=10 \mu\text{s}$ , parameter:  $T_{vj}$

Electrical Characteristics Diagrams

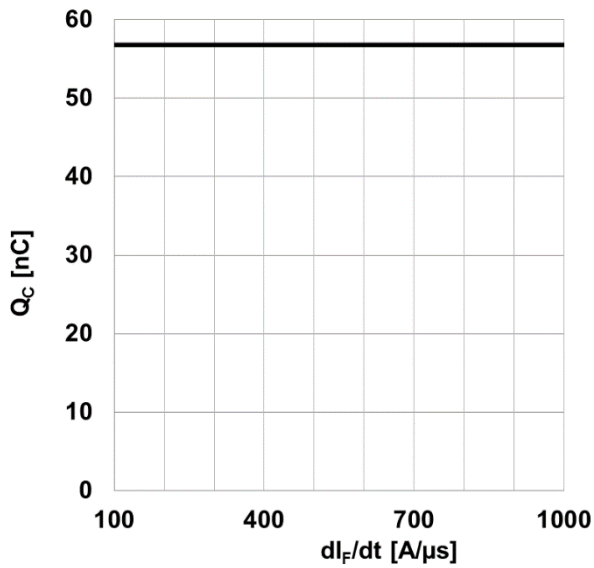


Figure 5. Typical capacitive charge as function of current slope,  $Q_c=f(dI_F/dt)$ ,  $T_{vj}=150^{\circ}C$

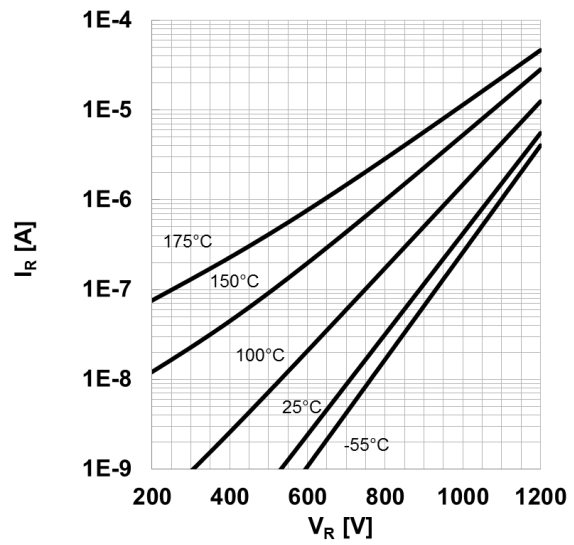


Figure 6. Typical reverse characteristics,  $I_R=f(V_R)$ , parameter:  $T_{vj}$

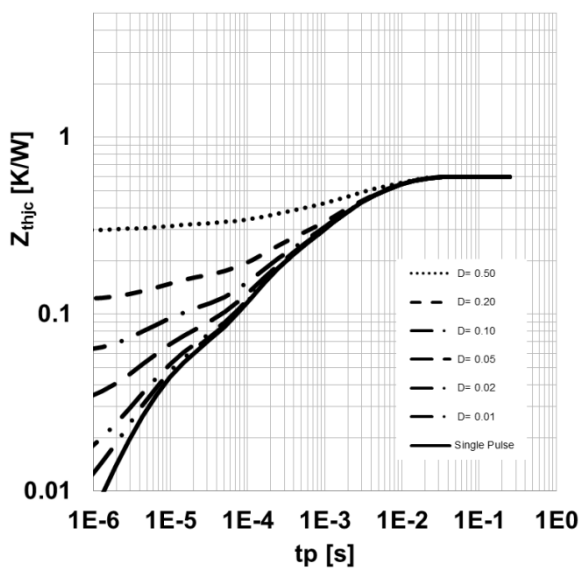


Figure 7. Max. transient thermal impedance,  $Z_{th,j-c}=f(t_p)$ , parameter:  $D=t_p/T$

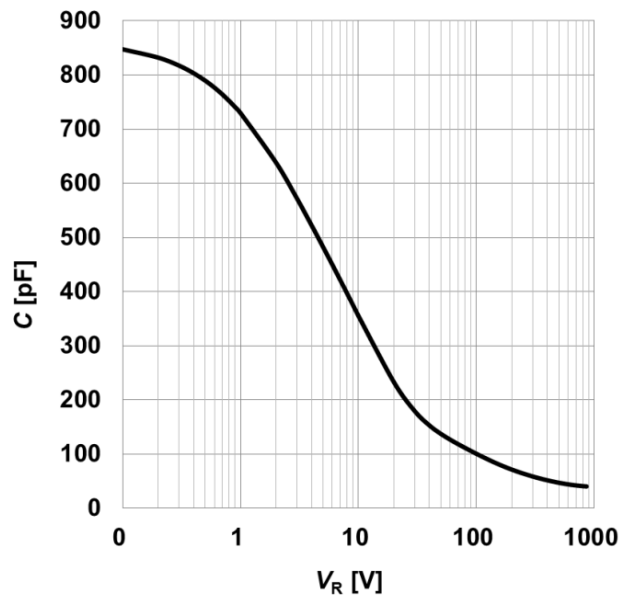
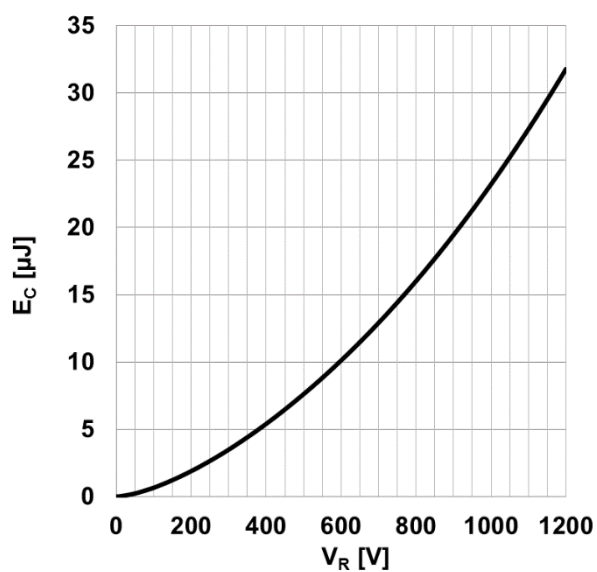


Figure 8. Typical capacitance as function of reverse voltage,  $C=f(V_R)$ ;  $T_{vj}=25^{\circ}C$ ;  $f=1\text{ MHz}$

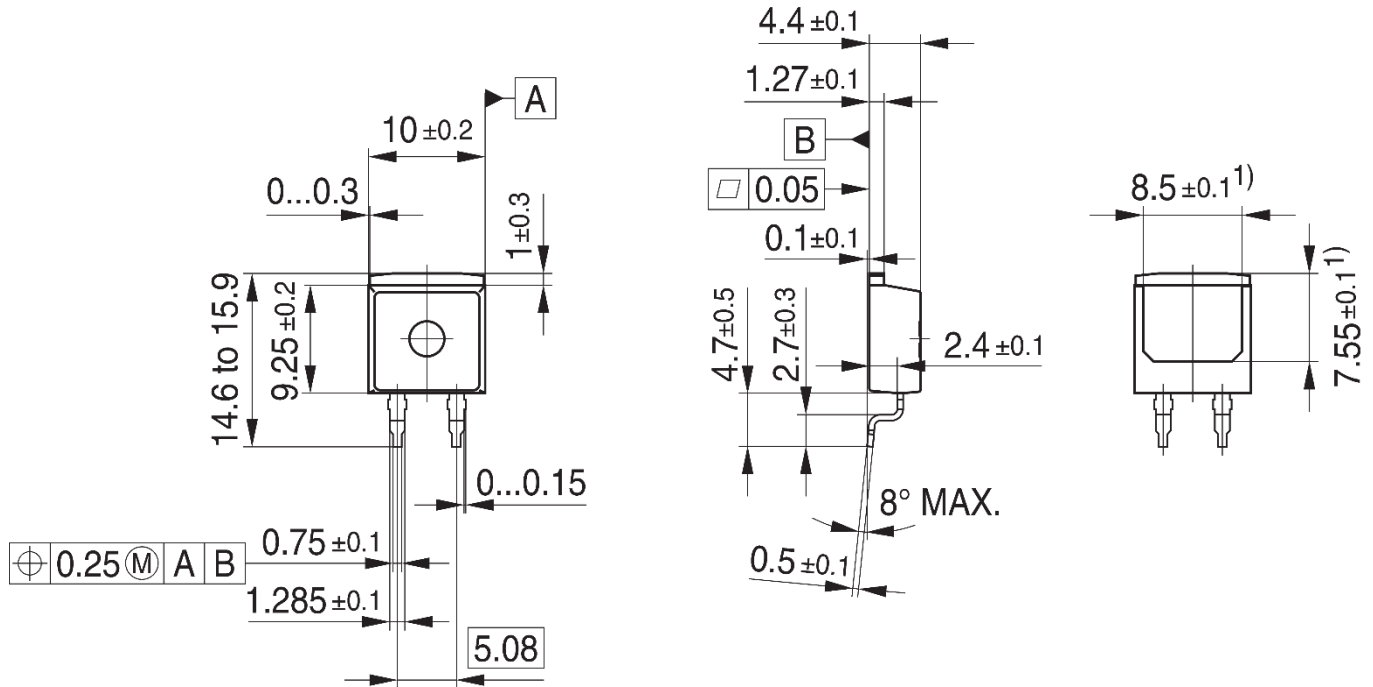




**Figure 9. Typical capacitively stored energy as function of reverse voltage,  $E_C=f(V_R)$**

5 Package Drawing

PG-T0263-2



- 1) Typical  
 Metal surface min. X = 7.25, y = 6.9  
 All metal surfaces: tin plated, except area of cut

All dimensions do not include mold flash or protrusions  
 All dimensions are in units mm  
 The drawings is in compliance with ISO 128-30, Projection Method 1 [ ]

### Revision history

### Revision history

Document version	Date of release	Description of changes
V 1.0	2019-01-25	Preliminary Datasheet
V 2.0	2019-10-28	Final Datasheet

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